
Design of Analog CMOS Integrated Circuits

<Chapter 3>

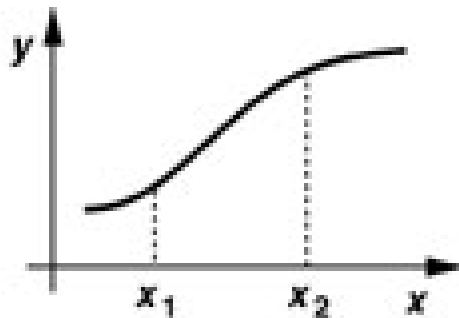
Single Stage Amplifier

양병도

3.1 Basic concepts

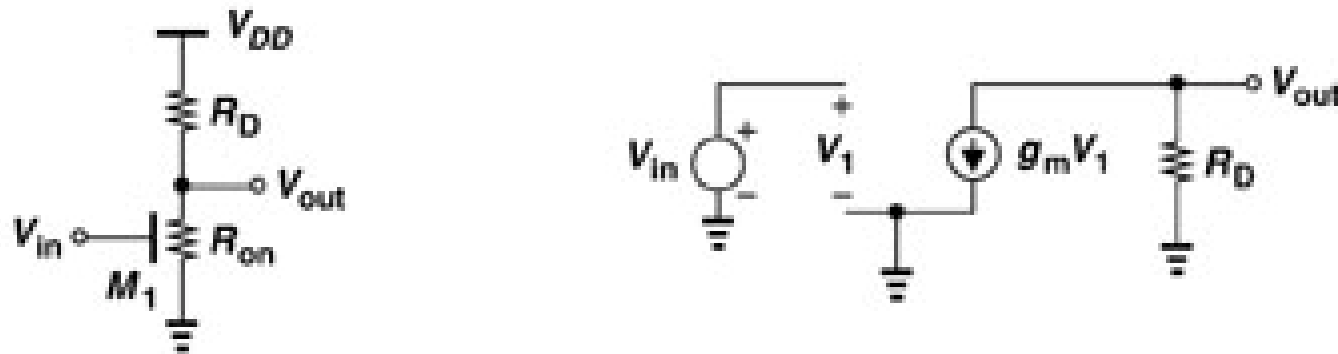
□ MOSFET은 non-linear 함수 → small signal은 linear 함수로 사용

- ✓ $y(t) \approx \alpha_0 + \alpha_1 x(t) + \alpha_2 x^2(t) + \dots + \alpha_n x^n(t)$
- ✓ where $x(t)$ and $y(t)$ may be current or voltage.
- ✓ For a sufficiently narrow range of x ,
- ✓ $y(t) \approx \alpha_0 + \alpha_1 x(t)$
- ✓ where α_0 can be considered the operating (bias) point and α_1 the small signal gain.



Non-linear system

3.2 Common Source



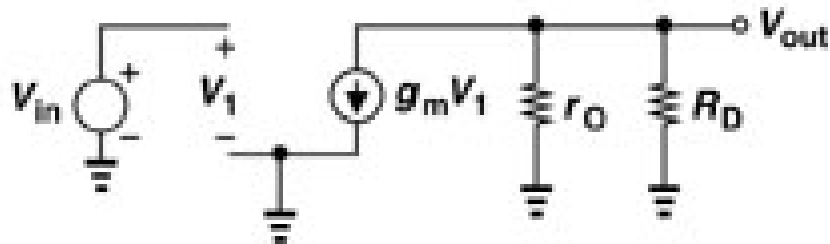
$$V_{out} = V_{DD} - R_D \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{in} - V_{TH})^2$$

$$A_v = \frac{\partial V_{out}}{\partial V_{in}} = -R_D \mu_n C_{ox} \frac{W}{L} (V_{in} - V_{TH}) = -g_m R_D$$

$$A_v = -g_m R_D$$

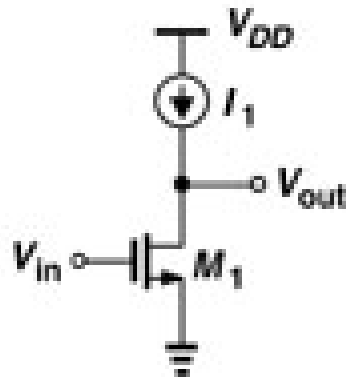
Common Source (cont.)

□ Channel length modulation 고려시



$$A_v = -g_m r_o \parallel R_D$$

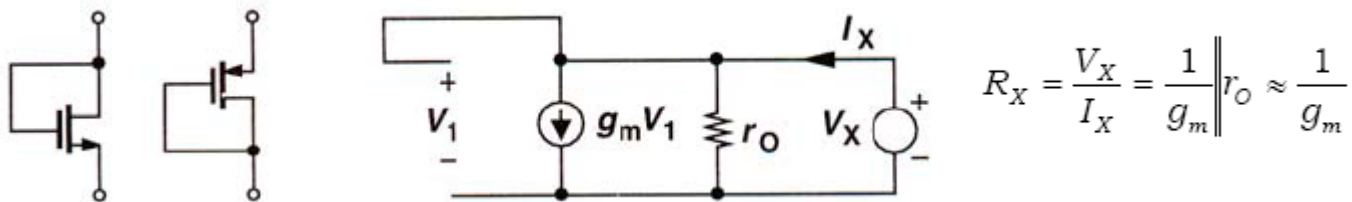
□ Ex 2.5



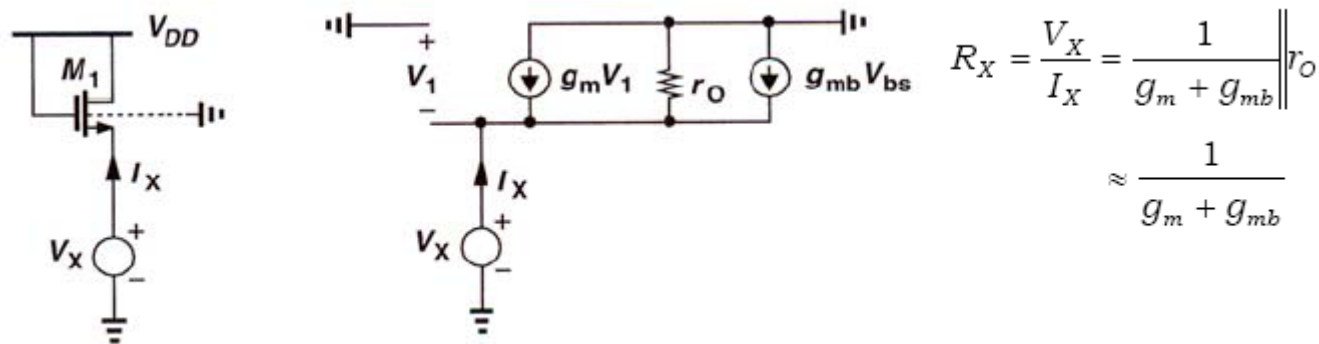
$$A_v = -g_m r_o = -g_m \frac{1}{\lambda I_D}$$

Common Source with Diode-Connected Load

□ R_D 대신 MOS diode로 저항 사용

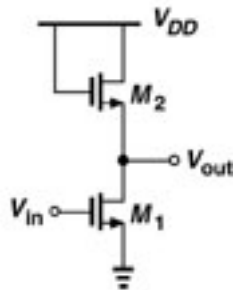


□ Body-effect 고려 → g_{mb} 추가



CS with Diode-Connected Load (cont.)

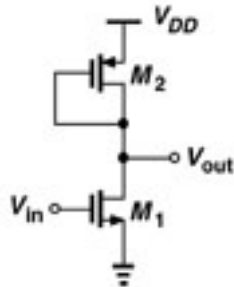
□ NMOS diode로 저항 사용 → body-effect → g_{mb} 추가



$$A_v = -g_{m1} \frac{1}{g_{m2} + g_{mb2}} = -\frac{g_{m1}}{g_{m2}} \frac{1}{1 + \eta}$$

$$A_v = -\sqrt{\frac{(W/L)_1}{(W/L)_2}} \frac{1}{1 + \eta}$$

□ PMOS diode로 저항 사용 → body-effect 없음



$$A_v = -g_{m1} \frac{1}{g_{m2}} = -\frac{g_{m1}}{g_{m2}}$$

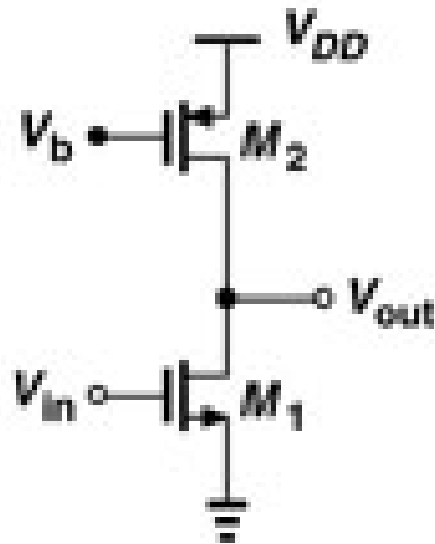
$$A_v = -\sqrt{\frac{u_n (W/L)_1}{u_p (W/L)_2}}$$

□ Channel-length modulation 고려

$$A_v = -g_{m1} \left(\frac{1}{g_{m2}} \parallel r_{o1} \parallel r_{o2} \right)$$

CS with Current Source Load

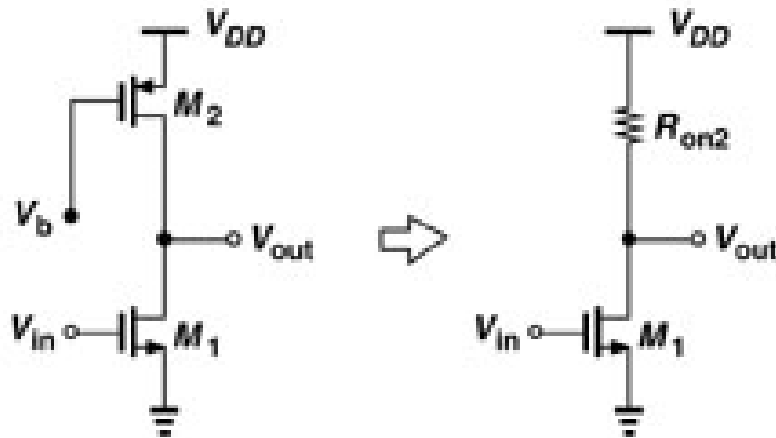
- Load의 Gate 전압이 변하지 않으므로 V_{DS} 의 전압이 줄어도 동작
→ V_{out} swing 전압이 커진다.



$$A_v = -g_m (r_{o1} \parallel r_{o2})$$

CS with Triode Region Load

□ V_b 가 V_{DD} 에 근접하면 load가 triode 동작에서 저항처럼 보인다.

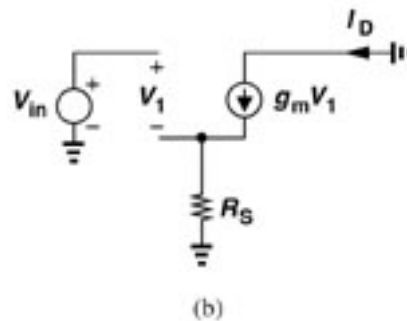
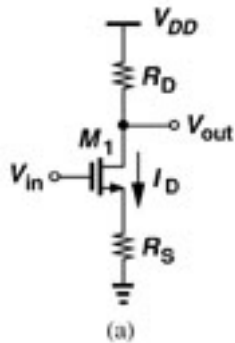


$$A_v = -g_m R_{ON2}$$

$$R_{ON2} = \frac{1}{\mu_n C_{ox} \left(\frac{W}{L} \right)_2 (V_{DD} - V_b - |V_{THP}|)}$$

CS with Source Degeneration

- ❑ 단점 → gain이 줄어든다.
- ❑ 장점 → gain이 저항으로만 이루어져 안정적이고 주파수 특성이 좋다.



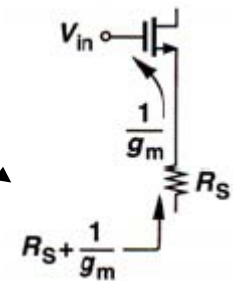
$$v_{in} = v_{gs} + R_s g_m v_{gs} = (1 + R_s g_m) v_{gs}$$

$$v_{gs} = \frac{v_{in}}{1 + R_s g_m}$$

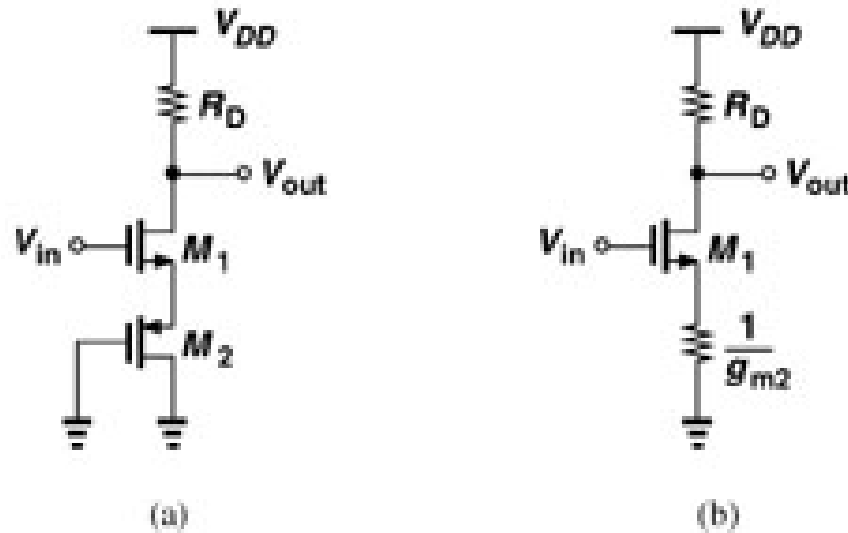
$$v_{out} = -R_D \times g_m v_{gs} = -\frac{R_D g_m}{1 + g_m R_s} v_{in}$$

$$A_v = \frac{-g_m R_D}{1 + g_m R_s} = \frac{-R_D}{1/g_m + R_s}$$

$$A_v \approx -\frac{R_D}{R_s} \quad (g_m \ll R_s)$$



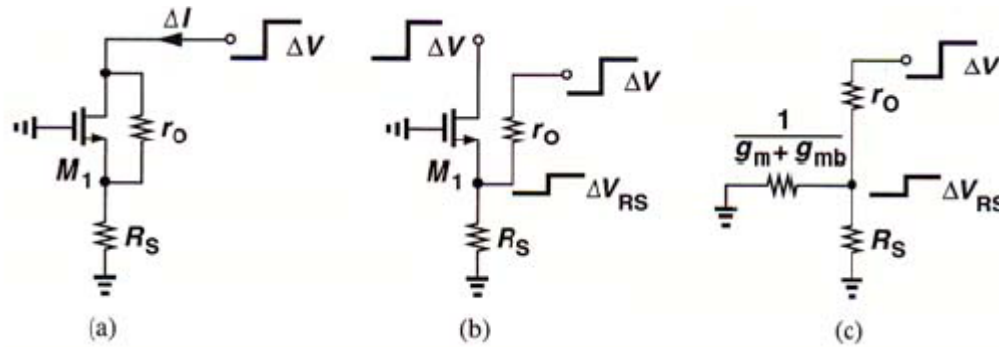
CS with Source Degeneration



□ Ex. 3.5

- ✓ M_2 is “diode-connected” $\rightarrow$ 저항 $1/g_{m2}$ 으로 보인다.
- ✓ $A_v = -R_D / (1/g_{m1} + 1/g_{m2})$

CS Output Resistance

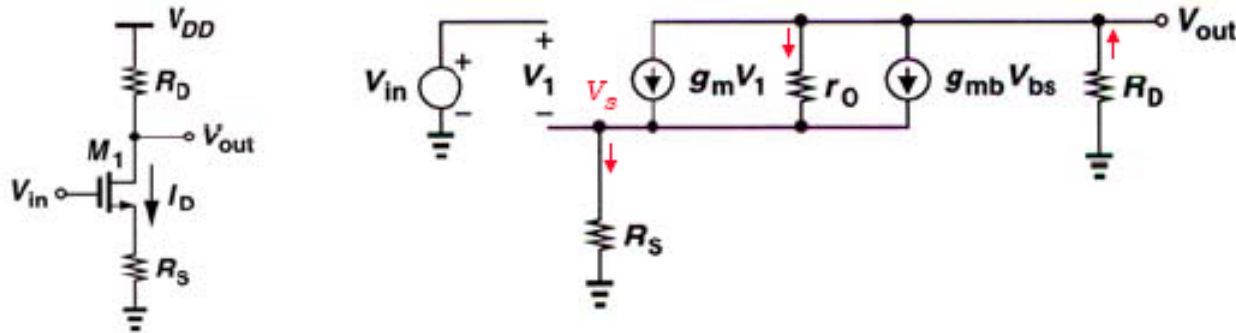


$$\Delta V_{RS} = \Delta V \frac{\frac{1}{g_m + g_{mb}} // R_S}{\frac{1}{g_m + g_{mb}} // R_S + r_o}$$

$$\Delta I = \frac{\Delta V_{RS}}{R_S} = \Delta V \frac{1}{[1 + (g_m + g_{mb})R_S]r_o + R_S}$$

$$\frac{\Delta V}{\Delta I} = [1 + (g_m + g_{mb})R_S]r_o + R_S = R_{out}$$

CS with Source Denegeneration (cont.)



$$I_{ro} = -\frac{V_{out}}{R_D} - (g_m V_1 + g_{mb} V_{bs}) = -\frac{V_{out}}{R_D} - \left[g_m \left(V_{in} + V_{out} \frac{R_S}{R_D} \right) + g_{mb} V_{out} \frac{R_S}{R_D} \right]$$

$$V_{out} = I_{ro} r_o - \frac{V_{out}}{R_D} R_S = -\frac{V_{out}}{R_D} r_o - \left[g_m \left(V_{in} + V_{out} \frac{R_S}{R_D} \right) + g_{mb} V_{out} \frac{R_S}{R_D} \right] r_o - V_{out} \frac{R_S}{R_D}$$

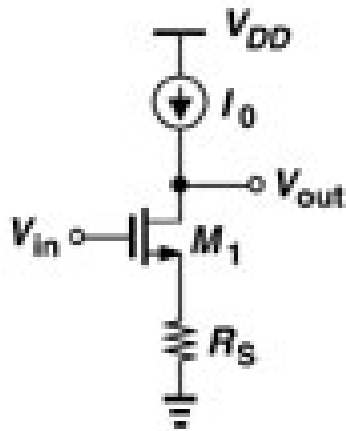
It follows that
$$\frac{V_{out}}{V_{in}} = \frac{-g_m r_o R_D}{R_D + R_S + r_o + (g_m + g_{mb}) R_S r_o} = \frac{-g_m r_o R_D}{R_D + R_{out}}$$

Let us rewrite as
$$A_v = -\frac{g_m r_o}{R_S + r_o + (g_m + g_{mb}) R_S r_o} \cdot \frac{R_D [R_S + r_o + (g_m + g_{mb}) R_S r_o]}{R_D + R_S + r_o + (g_m + g_{mb}) R_S r_o}$$

$$= -G_m (R_D // R_{out})$$

CS Gain Example

□ Ex. 3.6



$$\begin{aligned} A_v &= -G_m R_{out} \\ &= -\frac{g_m r_o}{R_{out}} R_{out} \\ &= -g_m r_o \end{aligned}$$

3.3 Source Follower (Common-Drain)

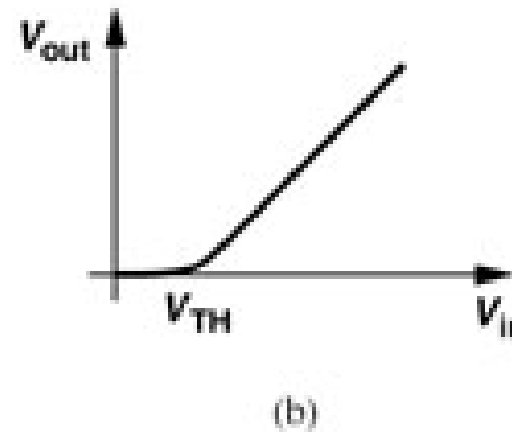
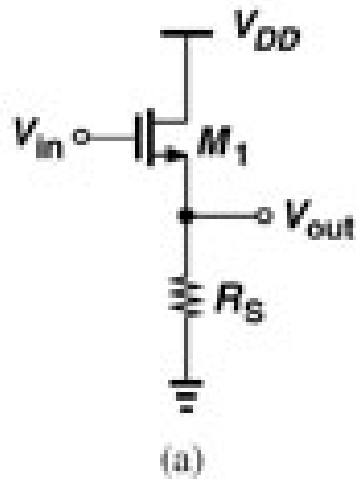
❑ Buffering Action

- ✓ Common Source 는 high gain을 얻기 위해 R_L 이 커야 한다.
- ✓ R_L 이 낮은 load를 drive 하기 위해 buffer 필요

❑ Buffer

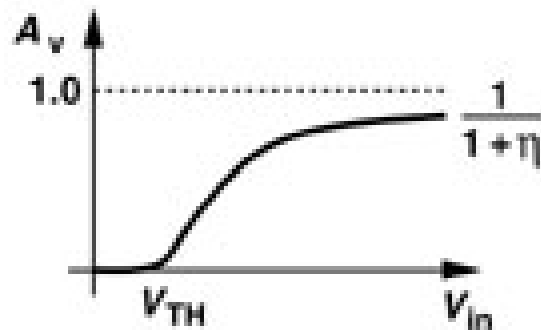
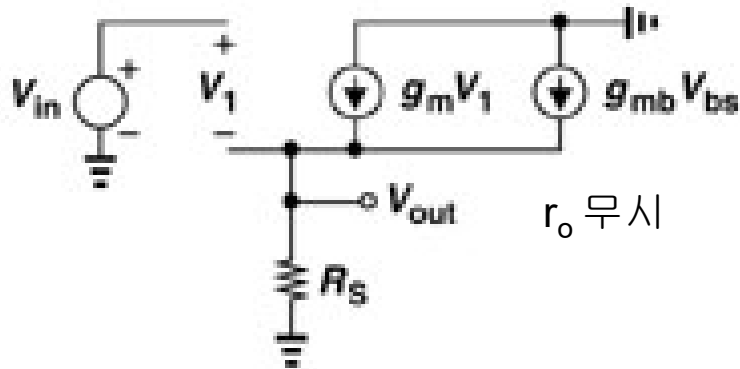
- ✓ $A_v=1$
- ✓ $R_{in}=\infty$

Large Signal Behavior



- If $V_{in} < V_{TH} \rightarrow M_1$ 은 off.
- If $V_{in} > V_{TH} \rightarrow M_1$ 은 Saturation 에서 동작
- Body Effect:
 - ✓ $I_D \uparrow \rightarrow V_S = I_D R_S \uparrow \rightarrow V_{SB} \uparrow \rightarrow V_{TH} \uparrow$
- $I_D \approx (V_G - V_{TH})/R_S$

Source Follower Gain



Gain Dependence on V_G

$$V_{in} - V_1 = V_{out}$$

$$V_{bs} = -V_{out}$$

$$V_{out} = R_S (g_m V_1 + g_{mb} V_{bs})$$

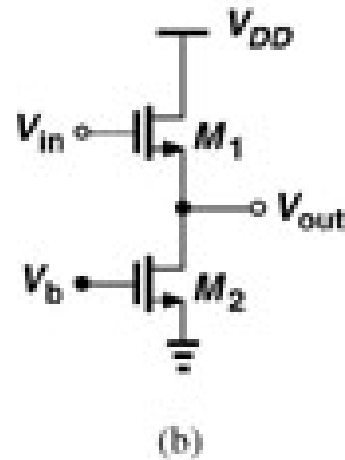
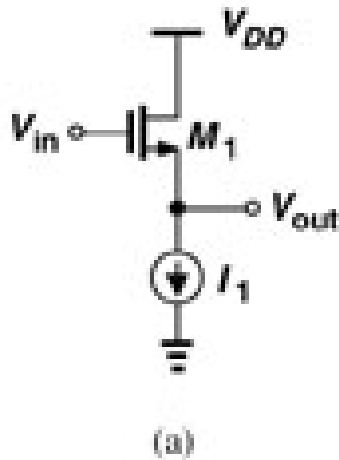
V_{in} 과 V_{bs} 를 넣고 정리하면

$$A_v = \frac{V_{out}}{V_{in}} = \frac{g_m R_S}{1 + (g_m + g_{mb}) R_S}$$

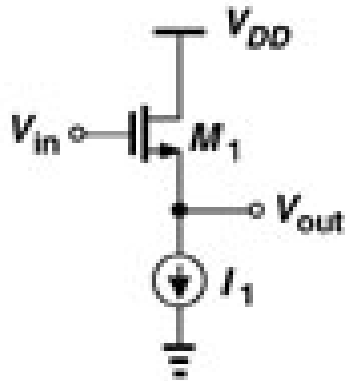
$$A_v = \frac{g_m R_S}{1 + g_m (1 + \eta) R_S} \approx \frac{1}{1 + \eta}$$

Problem with R_S

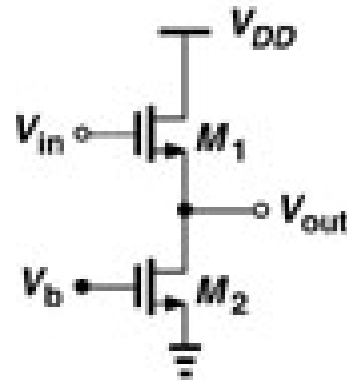
- V_{in} 가 변하면 $\rightarrow V_S$ 변화 $\rightarrow I_D$ 변화 $\rightarrow g_m$ 변화 $\rightarrow$ gain 변화 $\rightarrow$ nonlinearity.
- 해결: $R_S \rightarrow$ Current Source $\rightarrow I_D$ 유지



Example 3.7



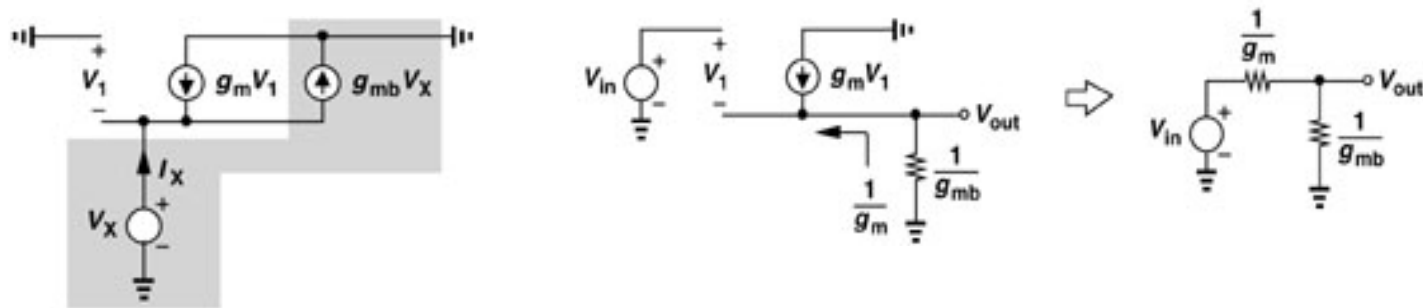
(a)



(b)

- ❑ Let $(W/L)_1=20/0.5$, $I_1=200\mu\text{A}$, $V_{\text{THO}}=0.6\text{V}$, $2\Phi_F=0.7\text{V}$, $\mu_n C_{\text{OX}}=50\mu\text{A}/\text{V}^2$, $\gamma=0.4\text{V}^{1/2}$
- ❑ $V_{\text{in}}=1.2\text{V}$ 일 때, V_{out} ?
 - ✓ Current: $(V_{\text{in}}-V_{\text{TH}}-V_{\text{out}})^2 = 2I_D/\mu_n C_{\text{OX}}(W/L)_1 \rightarrow V_{\text{out}} \approx 0.153\text{V}$
 - ✓ 위 결과 대입 $\rightarrow V_{\text{TH}} \approx V_{\text{THO}} + \gamma((2\Phi_F+V_{\text{out}})^{1/2}-(2\Phi_F)^{1/2}) \approx 0.635\text{V}$
 - ✓ 위 결과를 current 계산에 다시 대입 $\rightarrow V_{\text{out}} \approx 0.119\text{V}$,
- ❑ M_2 is in saturation, $(W/L)_2$ 의 최소 크기는?
 - ✓ $V_{\text{out}}=V_{\text{DS2}}=0.119\text{V} \geq V_{\text{b}}-V_{\text{TH2}} = [2I_D/\mu_n C_{\text{OX}}(W/L)_2]^{1/2}$
 - ✓ $(W/L)_2 \geq 283/0.5$

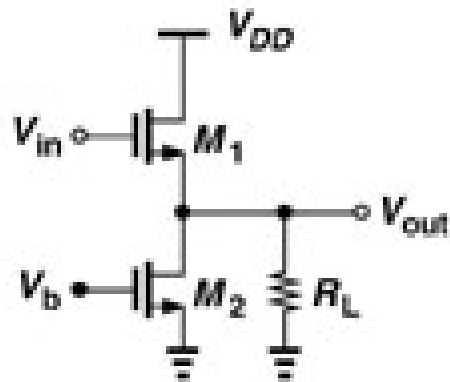
Gain of Source Follower with Current Source



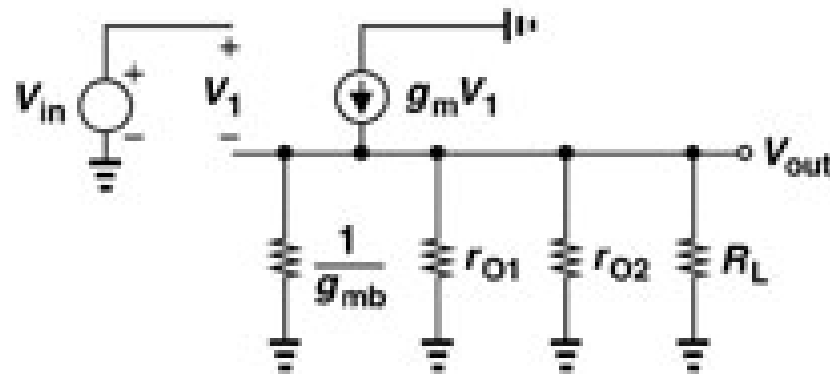
□ voltage gain

$$A_V = \frac{1}{\frac{1}{g_m} + \frac{1}{g_{mb}}} = \frac{g_m}{g_m + g_{mb}}$$

Source Follower with NMOS Current Source and R_L Loads



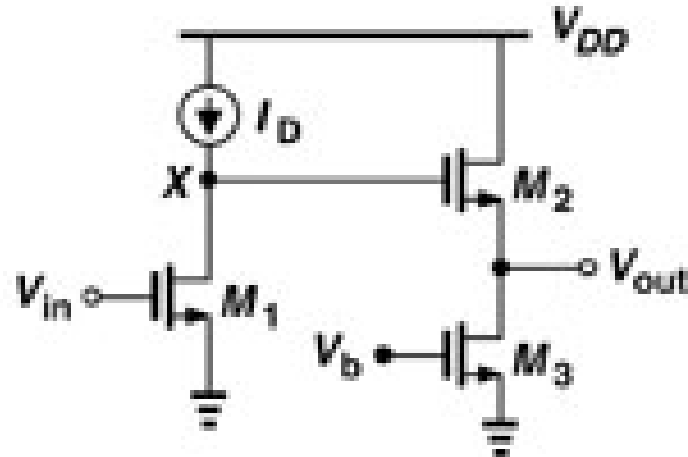
(a)



(b)

$$A_v = \frac{\frac{1}{g_{mb1}} \parallel r_{o1} \parallel r_{o2} \parallel R_L}{\left(\frac{1}{g_{mb1}} \parallel r_{o1} \parallel r_{o2} \parallel R_L\right) + \frac{1}{g_{m1}}}$$

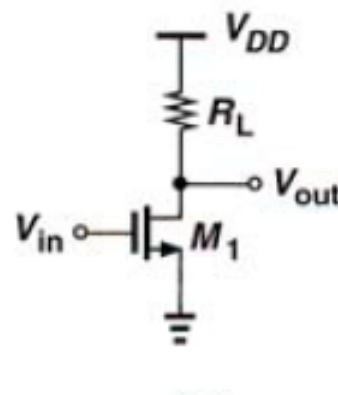
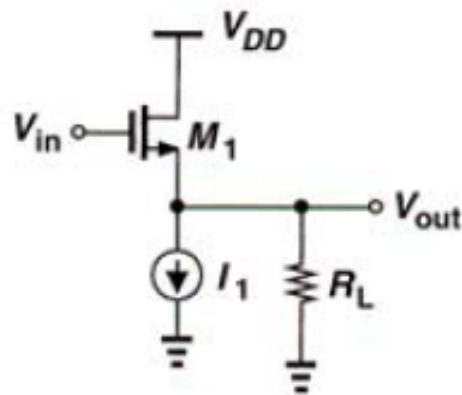
CS Amplifier + Source Follower



❑ Voltage headroom (swing) limitation

- ✓ CS amp. alone: $V_X \geq V_{GS1} - V_{TH1}$ to assure that M_1 is in Saturation.
- ✓ CS amp + Source Follower: $V_X \geq V_{GS2} + (V_{GS3} - V_{TH3})$ to assure that M_3 is in Saturation.

Poor Driving Capability

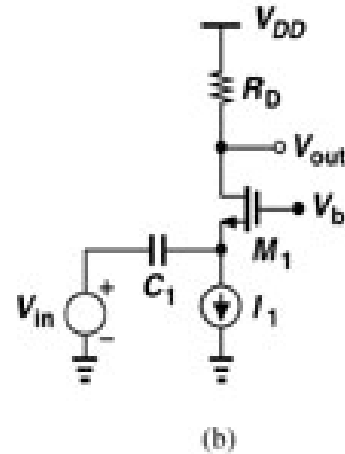
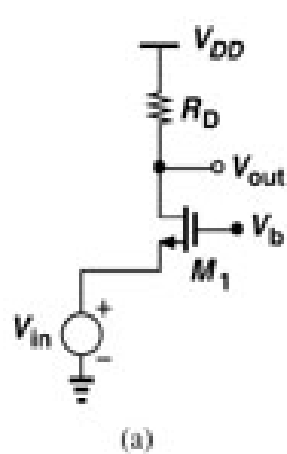


$$\left. \frac{V_{out}}{V_{in}} \right|_{SF} \approx \frac{R_L}{R_L + \frac{1}{g_{m1}}}$$

$$\left. \frac{V_{out}}{V_{in}} \right|_{CS} \approx g_{m1} R_L$$

□ R_L 이 작아지면 source follower의 gain이 크게 준다.

3.4 Common-Gate Amplifier



□ $A_V = g_m R_D$

□ $R_{in} = 1 / g_m$

□ $R_{out} = R_D // r_o$

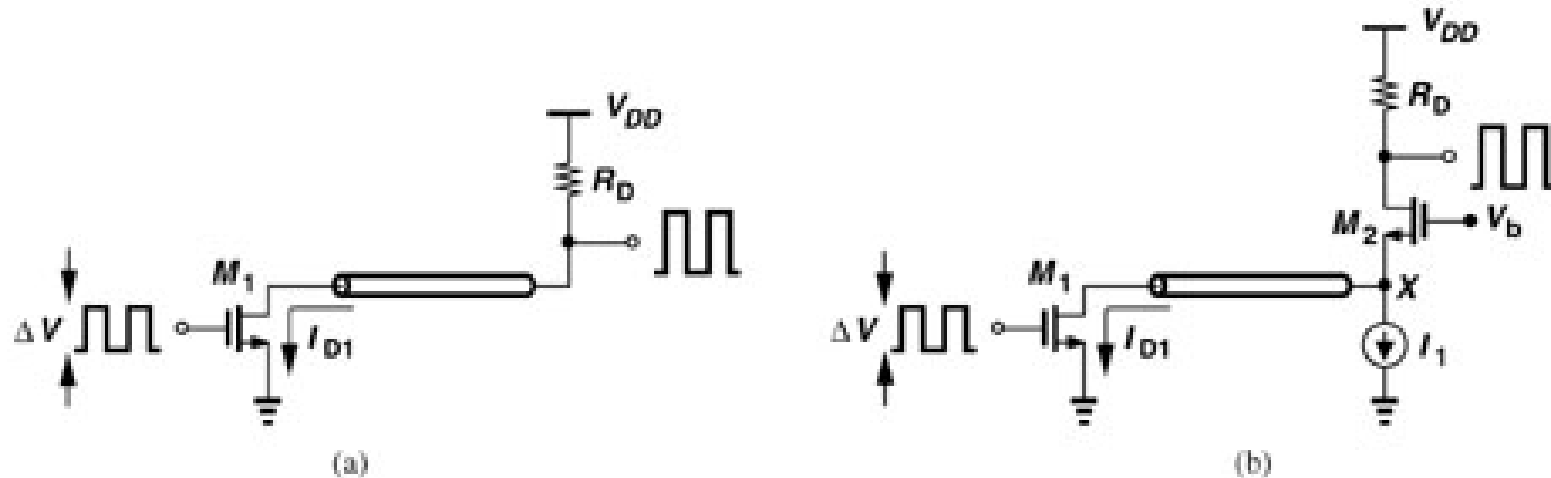
□ body Effect 고려 $\rightarrow V_{gs}$ 와 V_{bs} 가 똑같이 V_{in} 에 영향을 받음

✓ $g_m \rightarrow g_m + g_{mb} = g_m(1+\eta)$

✓ $A_V = g_m(1+\eta) R_D$

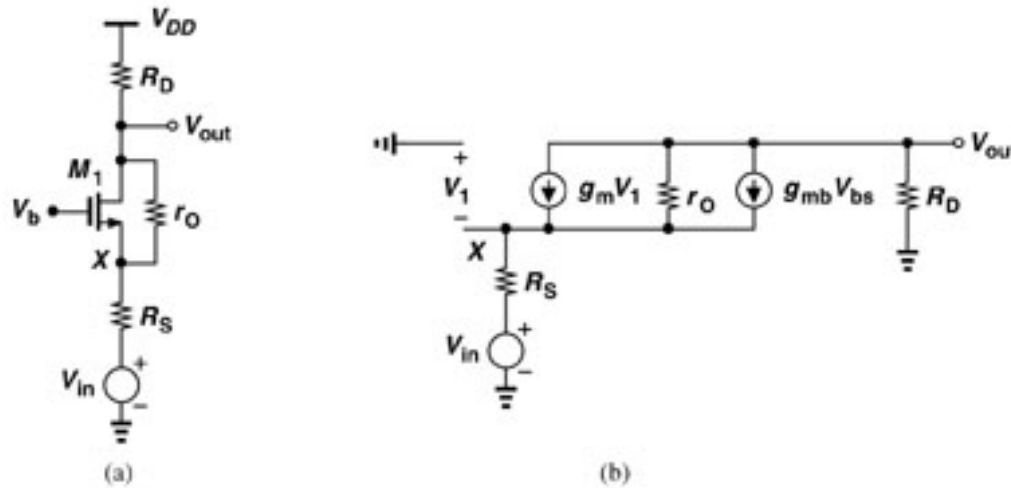
✓ $R_{in} = 1 / g_m(1+\eta)$

Low R_{in} of CG Amplifiers is useful if signal comes from a transmission line



- ❑ Assume: 50Ω transmission line
- ❑ If $\lambda=\gamma=0$, $\rightarrow$ 둘 회로가 같은 gain $A_v \approx -g_m R_D$.
- ❑ (a) $R_D = 50\Omega$ for no reflections $\rightarrow$ gain이 작다.
- ❑ (b) $R_{in} = 1/g_m(1+\eta) = 50\Omega \rightarrow R_D$ 를 크게 할 수 있다. $\rightarrow$ gain이 크다.

CG Amplifier – r_o 와 R_s 고려



$$A_v = \frac{(g_m + g_{mb})r_o + 1}{r_o + (g_m + g_{mb})r_o R_s + R_s + R_D} R_D$$

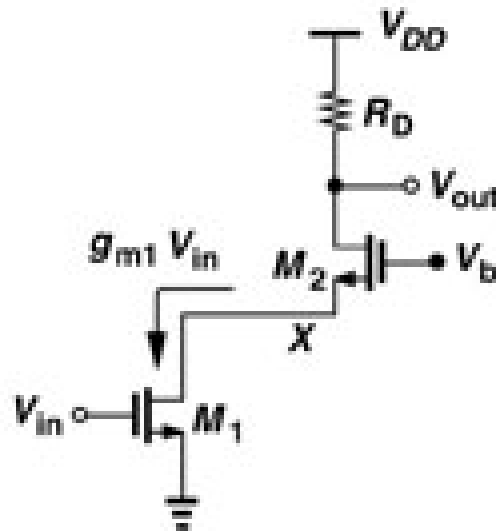
$$R_{in} = \frac{1}{g_m + g_{mb}} + \frac{R_D}{(g_m + g_{mb})r_o}$$

$$R_{out} = \{[1 + (g_m + g_{mb})r_o]R_s + r_o\} \parallel R_D$$

CG Amplifier의 특징

- Voltage gain = CS amplifier와 같다.
- Current gain = 1 $\rightarrow$ current buffer.
- 입력 저항 작다.
- 출력 저항 크다.

3.5 Cascode stage



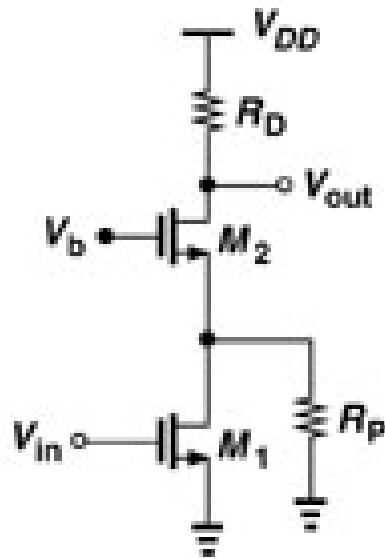
□ CS + CG

- ✓ Current gain은 CS에서 발생
- ✓ CG는 current buffer
- ✓ $A_V = -g_m R_D \rightarrow$ CS와 같은 gain

□ M1과 M2 saturation에서 동작

- ✓ 출력 전압의 swing 범위가 줄어든다.
- ✓ $V_b \geq V_{GS2} + V_{in} - V_{TH1}$
- ✓ $V_{out} \geq V_{in} - V_{TH1} + V_{GS2} - V_{TH2}$

EX 3.14



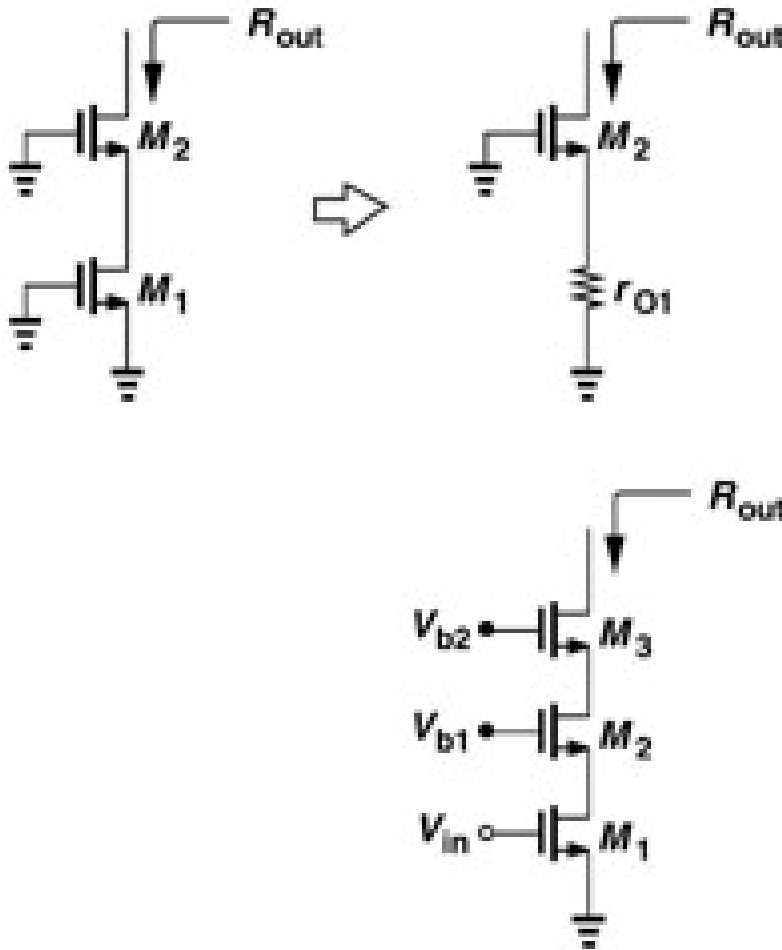
□ A_v ?

- ✓ $\lambda=0$
- ✓ $I_{D1} = g_{m1} V_{in}$
- ✓ I_{D1} 은 R_D 와 I_{D2} 로 전류가 나뉨.
- ✓ $\rightarrow$ current divider
- ✓ $A_v = I_{D2} / V_{in}$

$$I_{D2} = g_{m1} V_{in} \frac{R_p}{R_p + \frac{1}{g_{m2} + g_{mb2}}} = g_{m1} V_{in} \frac{R_p (g_{m2} + g_{mb2})}{R_p (g_{m2} + g_{mb2}) + 1}$$

$$A_v = -g_{m1} \frac{R_p R_D (g_{m2} + g_{mb2})}{R_p (g_{m2} + g_{mb2}) + 1}$$

Output Resistance



- CS에서 degeneration 저항을 가진 경우와 같다.
- Cascode로 연결된 경우 r_{o1} 이 $r_{o2}(g_{m2}+g_{mb2})$ 배 크게 보인다.

$$R_{out} = [1 + (g_{m2} + g_{mb2})r_{o2}]r_{o1} + r_{o2}$$

$$\approx r_{o1}r_{o2}(g_{m2} + g_{mb2})$$

- Cascode의 수를 증가시키면 지속적으로 출력 저항이 크게 보인다.

EX 3.15

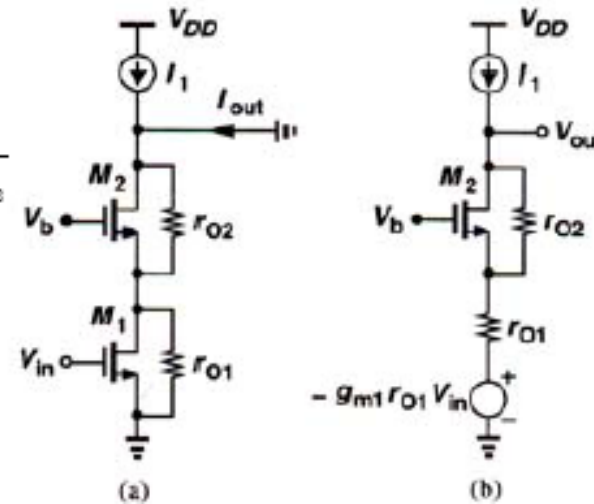
$$I_{out} = g_{m1} v_{in} \frac{r_{o1}}{r_{o1} + \frac{1}{g_{m2} + g_{mb2}} // r_{o2}}$$

$$G_m = g_{m1} \frac{r_{o1}}{r_{o1} + \frac{1}{g_{m2} + g_{mb2}} // r_{o2}} = \frac{g_{m1} r_{o1} [r_{o2} (g_{m2} + g_{mb2}) + 1]}{r_{o1} r_{o2} (g_{m2} + g_{mb2}) + r_{o1} + r_{o2}}$$

$$A_v = -G_m R_{out} = -g_{m1} r_{o1} [r_{o2} (g_{m2} + g_{mb2}) + 1]$$

If we had assumed $G_m = g_{m1}$,

then $A_v \approx -g_{m1} \{ [1 + (g_{m2} + g_{mb2}) r_{o2}] r_{o1} + r_{o2} \}$



□ A_v ?

✓ $I_{D1} = g_{m1} V_{in}$

✓ I_{D1} 은 r_{o1} 와 I_{out} 로 전류가 나뉨. → current divider

✓ $A_v = I_{out} / V_{in}$

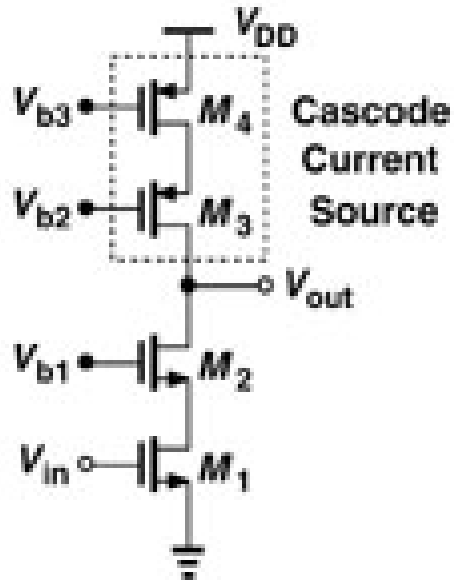
□ 쉽게 풀면, $G_m = g_m$ 으로 가정 후 R_{out} 을 곱함.

NMOS cascode amplifier with PMOS cascode load

□ PMOS current source 출력 저항 증가 → gain 증가

□ 출력 전압 swing 줄어듦

✓ $V_{DD} - (V_{GS1} - V_{TH1}) - (V_{GS2} - V_{TH2}) - |V_{GS3} - V_{TH3}| - |V_{GS4} - V_{TH4}|$



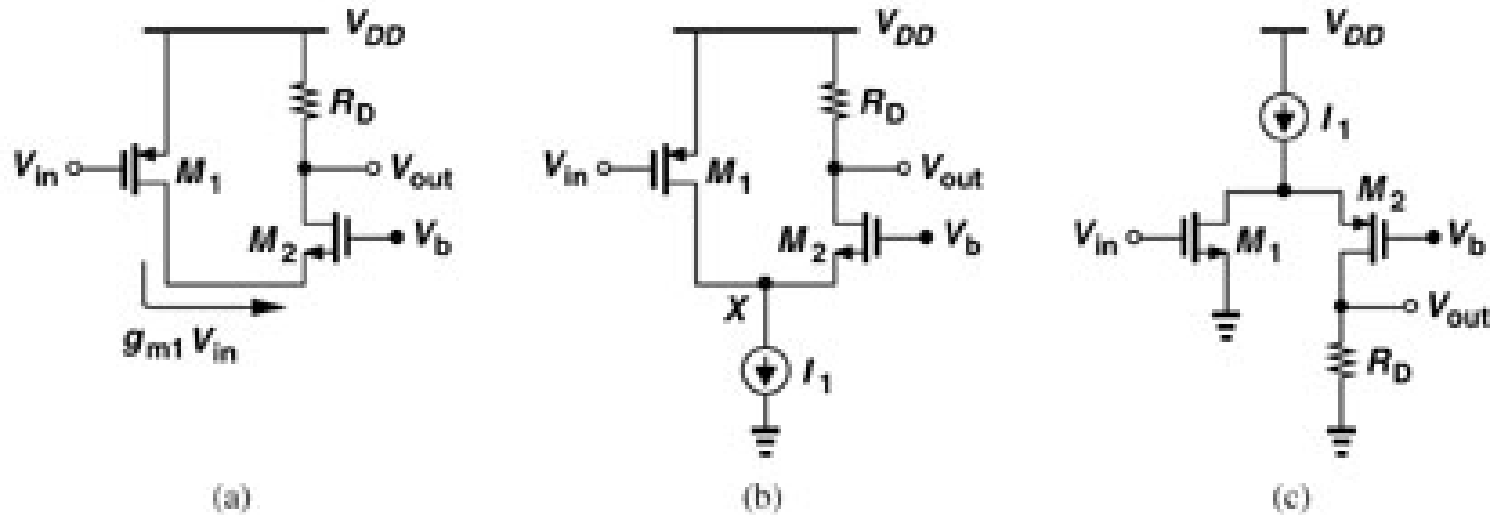
$$A_V \approx G_m R_{out}$$

$$R_{out} = \{[1 + (g_{m2} + g_{mb2})r_{o2}]r_{o1} + r_{o1}\} \parallel \{[1 + (g_{m3} + g_{mb3})r_{o3}]r_{o4} + r_{o3}\}$$

$$G_m \approx g_{m1}$$

$$A_V \approx g_{m1}[(r_{o1}r_{o2}g_{m2}) \parallel (r_{o3}r_{o4}g_{m3})]$$

Folded Cascode



- ❑ NMOS CS + PMOS CG or PMOS CS + NMOS CG
- ❑ Cascode 형태와 결과는 유사함
- ❑ DC current source 필요